

TRIAC



T Y P * * = V _{DRM}	V _{DRM}		I _T (RMS) A	I _T (RMS) bei A	T _C °C	I _{TSM} 10ms A	du/dt TYP V/μs	I _{GT} mA	I _H mA	T _{JM} °C	R _{thJC} °C/W	Gehäuse Case
	von V	bis V										
TAG 92-1...92-6	30	400	0,6	0,6	55	6		5 ¹	10	125	100	TO-92
TAG 92A1...92A6	30	400	0,6	0,6	55	6		5 ¹ 10 ²	10	125	100	TO-92
TAG 92B1...92B6	30	400	0,6	0,6	55	6		10 ¹ 20 ²	10	125	100	TO-92
TAG 200-*	100	400	2,0	1,6	70	35	20	25	25	105	17	TO-39
TAG 201-*	100	400	2,0	1,6	70	35	20	10	10	105	17	TO-39
TAG 202-*	100	400	4,0	2,5	70	35	50	10 ³	10	105	10	TO-39
TAG 202A-*	100	400	4,0	2,5	70	35	50	10	10	105	10	TO-39
TAG 203-*	100	400	4,0	2,5	70	35	10	5 ³	10	105	10	TO-39
TAG 203A-*	100	400	4,0	2,5	70	35	10	5	10	105	10	TO-39
TAG 204-*	100	400	4,0	2,5	60	35	5	3 ³	5	90	10	TO-39
TAG 204A-*	100	400	4,0	2,5	60	35	5	3	5	90	10	TO-39
TAG 205-*	100	400	4,0	2,5	70	40	200	25	25	105	10	TO-39
TAG 206-*	100	400	4,0	2,5	70	40	50	10	10	105	10	TO-39
TAG 136		400	3,0	3,0	70	30	10	25	15	100	6	TO-202
TAG 96-1...96-6	100	600	4,0	4,0	70			50	50	125	3	TO-126
TAG 240-*	200	800	6,5	5,0	70	60	500 ⁴	50	50	105	5	TO-220AB-I
TAG 241-*	200	800	6,5	5,0	70	60	200	25	25	105	5	TO-220AB-I
TAG 245-*	200	800	8,0	6,5	70	70	500 ⁴	50	50	105	5	TO-220AB-I
TAG 246-*	200	800	8,0	6,5	70	70	200	25	25	105	5	TO-220AB-I
TAG 220-*	200	800	8,0	6,0	70	60	200	25	25	105	3,3	TO-220AB
TAG 221-*	200	800	8,0	6,0	70	60	50	10	10	105	3,3	TO-220AB
TAG 222-*	200	800	8,0	6,0	70	60	10	5	10	105	3,3	TO-220AB
TAG 224-*	200	800	8,0	8,0	70	80	500 ⁴	50	50	105	2,5	TO-220AB
TAG 225-*	200	800	8,0	8,0	70	80	200	25	25	105	2,5	TO-220AB
TAG 226-*	200	800	8,0	8,0	70	80	50	10	10	105	2,5	TO-220AB
TAG 227-*	200	800	8,0	8,0	70	80	10	5	10	105	2,5	TO-220AB
TAG 250A-*	200	800	12,0	10,0	70	120	500 ⁴	50 ³	50	105	2,5	TO-220AB
TAG 250-*	200	800	12,0	10,0	70	120	500	50	50	105	2,5	TO-220AB
TAG 251-*	200	800	12,0	10,0	70	120	200	25	25	105	2,5	TO-220AB
TAG 255A-*	200	800	12,0	12,0	70	120	500 ⁴	50 ³	50	105	2,2	TO-220AB
TAG 255-*	200	800	12,0	12,0	70	120	500	50	50	105	2,2	TO-220AB
TAG 256-*	200	800	12,0	12,0	70	120	200	25	25	105	2,2	TO-220AB
TAG 280-*	200	800	16,0	15,0	70	150	500	50 ³	50	105	1,6	TO-220AB
TAG 285-*	200	800	20,0	20,0	70	200	500	50 ³	50	105	1,6	TO-220AB
TAG 306-*	50	600	6,0	6,0	70	80	20	50	50	105	3,5	TO-66
TAG 260-*	100	800	8,0	6,0	70	80	500	50	50	105	4,0	TO-66
TAG 261-*	100	800	8,0	6,0	70	80	200	25	25	105	4,0	TO-66
TAG 265-*	100	800	12,0	10,0	70	100	500	50 ³	50	105	2,8	TO-66
TAG 266-*	100	800	12,0	10,0	70	100	200	25	25	105	2,8	TO-66
TAG 325-*	600	1200	25,0	25,0	91	400	50	100	30	125	1,0	TO-49
2N6342A.2N6345A	200	800	12,0	12,0	80	120		50 ¹	50	105	2,0	TO-220AB
2N6346A.2N6349A	200	800	12,0	12,0	80	120		50 ³	50	105	2,0	TO-220AB

1 = I⁺, III⁻ 2 = I⁻, III⁺ 3 = EXCP III⁺ 4 = MIN

rev. 18.77.

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